



UTRON

Rev. 1.1

UT62L2568

256K X 8 BIT LOW POWER CMOS SRAM

REVISION HISTORY

REVISION	DESCRIPTION	Release Date
Preliminary Rev. 0.1	Original.	Jun 18, 2001
Rev. 1.0	- Revised Power supply 55ns (max.) for $V_{CC}=2.7V\sim3.6V$ 70/100ns (max.) for $V_{CC}=2.5V\sim3.6V$ - Revised DC ELECTRICAL CHARACTERISTICS : - Revised V_{IH} as 2.2V - Revised standby current I_{SB1} of LL-version Typical : $3\mu A \rightarrow 2\mu A$ Maximum : $25\mu A \rightarrow 20\mu A$ - Revised AC ELECTRICAL CHARACTERISTICS : - Revised t_{OH} as 10ns (min.) - Revised 36-pin TFBGA package outline dimension : - Rev. 0.1 ball diameter=0.3mm - Rev. 1.0 ball diameter=0.35mm	Jul 30, 2002
Rev. 1.1	- Revised "FEATURES" Operating current : $40/35/25mA(I_{CC} \text{ max}) \rightarrow 20/18/15mA(I_{CC} \text{ typ.})$ - TRUTH TABLE & DC ELECTRICAL : Delete I_{SB2} - Revised V_{TERM} : -0.5 to $V_{CC}+0.3V \rightarrow -0.5$ to 4.6V - Added V_{OH} : 2.7V at $V_{CC}=3.0V$ - Revised DC ($I_{CC} \text{ max}$) $45/35/25mA \rightarrow 35/30/25mA$ ($I_{CC} \text{ typ.}$) $30/25/20mA \rightarrow 20/18/15mA$ - Add under/overshoot range of V_{IL} & V_{IH} - Revised AC $t_{OHZ}^* @ 100ns$ (max): $35ns \rightarrow 30ns$ $t_{WHZ}^* \text{ (max)} : 30/30/40 \rightarrow 20/25/30ns$ - Revised "Data retention Characteristics" : $I_{DR-LL} \text{ (Typ.)} : NA \rightarrow 1\mu A$, $I_{DR-L} \text{ (Typ.)} : NA \rightarrow 10\mu A$ $I_{DR-LL} \text{ (Max.)} : 25\mu A \rightarrow 6\mu A$ $t_R \text{ (min)} : 5ns \rightarrow t_{RC}$ - Add order information for lead free product	Apr 28, 2003



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FEATURES

- Fast access time :
55ns(max.) for Vcc=2.7V~3.6V
70/100ns(max.) for Vcc=2.5V~3.6V
- CMOS low power operation
Operating : 20/18/15mA (TYP.)
Standby : 20 uA(TYP.) L -version
2 uA(TYP.) LL-version
- Single 2.5V~3.6V power supply
- Operating temperature:
Commercial : 0 ~70
Extended : -20 ~80
- All TTL compatible inputs and outputs
- Fully static operation
- Three state outputs
- Data retention voltage: 1.5V (min)
- Package : 32-pin 8mm x 20mm TSOP-
32-pin 8mm x 13.4mm STSOP-
36-pin 6mm x 8mm TFBGA

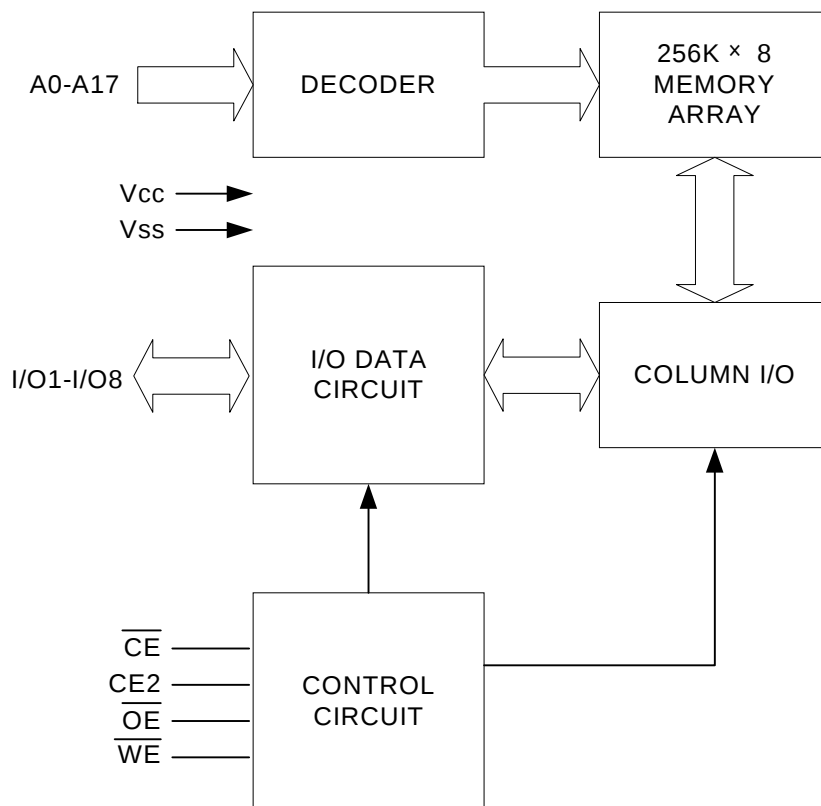
GENERAL DESCRIPTION

The UT62L2568 is a 2,097,152-bit low power CMOS static random access memory organized as 262,144 words by 8 bits. It is fabricated using high performance, high reliability CMOS technology.

The UT62L2568 is designed for very low power system applications. It is particularly well suited for battery back-up nonvolatile memory applications.

It operates from a wide range of 2.5V~ 3.6V supply voltage. Easy memory expansion is provided by using two chip enable input ($\overline{CE}$, CE2). And all inputs and three-state outputs are fully TTL compatible.

FUNCTIONAL BLOCK DIAGRAM





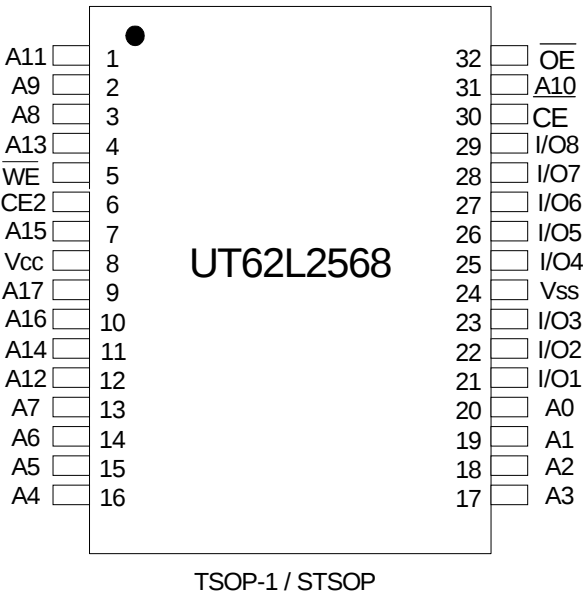
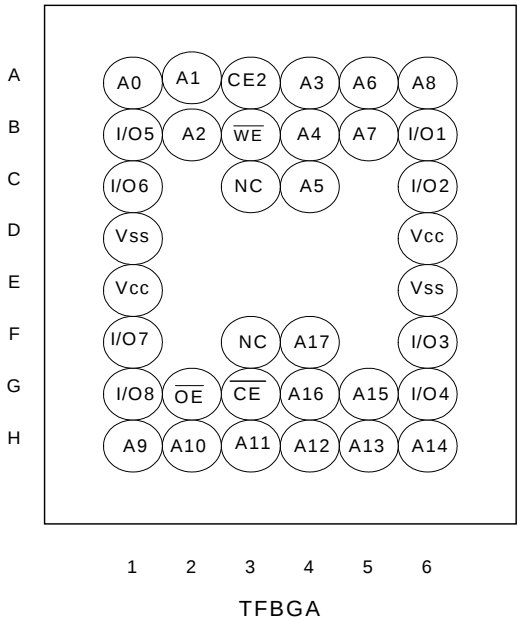
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PIN CONFIGURATION



PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 - A17	Address Inputs
I/O1 - I/O8	Data Inputs/Outputs
CE, CE2	Chip Enable Inputs
WE	Write Enable Input
OE	Output Enable Input
V _{CC}	Power Supply
V _{SS}	Ground
NC	No Connection



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TRUTH TABLE

MODE	$\overline{CE}$	CE2	$\overline{OE}$	$\overline{WE}$	I/O OPERATION	SUPPLY CURRENT
Standby	H	X	X	X	High - Z	I_{SB}, I_{SB1}
	X	L	X	X	High - Z	I_{SB}, I_{SB1}
Output Disable	L	H	H	H	High - Z	I_{CC}, I_{CC1}, I_{CC2}
Read	L	H	L	H	D_{OUT}	I_{CC}, I_{CC1}, I_{CC2}
Write	L	H	X	L	D_{IN}	I_{CC}, I_{CC1}, I_{CC2}

Note: H = V_{IH} , L = V_{IL} , X = Don't care.

ABSOLUTE MAXIMUM RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Terminal Voltage with Respect to V_{SS}	V_{TERM}	-0.5 to 4.6	V
Operating Temperature	Commercial	T_A	0 to 70
	Extended	T_A	-20 to 80
Storage Temperature	T_{STG}	-65 to 150	
Power Dissipation	P_D	1	W
DC Output Current	I_{OUT}	50	mA
Soldering Temperature (under 10 secs)	T_{solder}	260	

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

DC ELECTRICAL CHARACTERISTICS ($V_{CC} = 2.5V \sim 3.6V$, $T_A = 0$ to 70 / -20 to 80 (E))

PARAMETER	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Power Voltage	V _{CC}		55	2.7	3.0	3.6	V
			70/100	2.5	3.0	3.6	V
Input High Voltage	V _{IH} ^{*1}			2.2	-	V _{CC} +0.3	V
Input Low Voltage	V _{IL} ^{*2}			- 0.2	-	0.6	V
Input Leakage Current	I _{LI}	V _{SS}	V _{IN} V _{CC}	- 1	-	1	μA
Output Leakage Current	I _{LO}	V _{SS}	V _{I/O} V _{CC} , Output Disabled	- 1	-	1	μA
Output High Voltage	V _{OH}	I _{OH} = - 1mA (I _{OH} = -0.5mA when V _{CC} <2.7V)		2.2	2.7	-	V
Output Low Voltage	V _{OL}	I _{OL} = 2.1mA		-	-	0.4	V
Operating Current	I _{CC}	Cycle time=Min.100% duty, CE =V _{IL} and CE2 = V _{IH} , I _{I/O} =0mA	55	-	20	35	mA
			70	-	18	30	mA
			100	-	15	25	mA
	I _{CC1}	100%duty, I _{I/O} =0mA, CE 0.2V and CE2 V _{CC} -0.2V, other pins at 0.2V or V _{CC} -0.2V	TCycle= 1μs	-	4	5	mA
	I _{CC2}		TCycle= 500ns	-	8	10	mA
	Standby Current (TTL)	I _{SB}	CE =V _{IH} or CE2 = V _{IL}		-	0.3	0.5
Standby Current (CMOS)	I _{SB1}	CE =V _{CC} -0.2V or CE2=0.2V, other pins at 0.2V or V _{CC} -0.2V	-L	-	20	80	μA
			-LL	-	2	20	μA

Notes:

1. Overshoot : $V_{CC}+3.0v$ for pulse width less than 10ns.
2. Undershoot : $V_{SS}-3.0v$ for pulse width less than 10ns.
3. Overshoot and Undershoot are sampled, not 100% tested.



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CAPACITANCE ($T_A=25^\circ\text{C}$, $f=1.0\text{MHz}$)

PARAMETER	SYMBOL	MIN.	MAX	UNIT
Input Capacitance	C_{IN}	-	6	pF
Input/Output Capacitance	$C_{I/O}$	-	8	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Input Pulse Levels	0V to 3V
Input Rise and Fall Times	5ns
Input and Output Timing Reference Levels	1.5V
Output Load	$C_L = 30\text{pF}+1\text{TTL}$, $I_{OH} = -1\text{mA}$, $I_{OL} = 2.1\text{mA}$

AC ELECTRICAL CHARACTERISTICS ($T_A = 0^\circ\text{C}$ to 70°C / -20°C to 80°C (E))

(1) READ CYCLE

PARAMETER	SYMBOL	UT62L2568-55 $V_{CC} = 2.7\text{V}\sim 3.6\text{V}$		UT62L2568-70 $V_{CC} = 2.5\text{V}\sim 3.6\text{V}$		UT62L2568-100 $V_{CC} = 2.5\text{V}\sim 3.6\text{V}$		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	t_{RC}	55	-	70	-	100	-	ns
Address Access Time	t_{AA}	-	55	-	70	-	100	ns
Chip Enable Access Time	t_{ACE}	-	55	-	70	-	100	ns
Output Enable Access Time	t_{OE}	-	30	-	35	-	50	ns
Chip Enable to Output in Low Z	t_{CLZ*}	10	-	10	-	10	-	ns
Output Enable to Output in Low Z	t_{OLZ*}	5	-	5	-	5	-	ns
Chip Disable to Output in High Z	t_{CHZ*}	-	20	-	25	-	30	ns
Output Disable to Output in High Z	t_{OHZ*}	-	20	-	25	-	30	ns
Output Hold from Address Change	t_{OH}	10	-	10	-	10	-	ns

(2) WRITE CYCLE

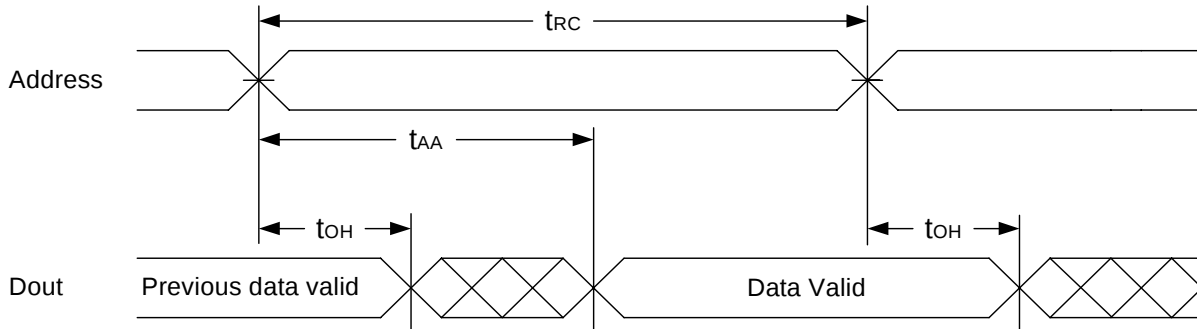
PARAMETER	SYMBOL	UT62L2568-55 $V_{CC} = 2.7\text{V}\sim 3.6\text{V}$		UT62L2568-70 $V_{CC} = 2.5\text{V}\sim 3.6\text{V}$		UT62L2568-100 $V_{CC} = 2.5\text{V}\sim 3.6\text{V}$		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	t_{WC}	55	-	70	-	100	-	ns
Address Valid to End of Write	t_{AW}	50	-	60	-	80	-	ns
Chip Enable to End of Write	t_{CW}	50	-	60	-	80	-	ns
Address Set-up Time	t_{AS}	0	-	0	-	0	-	ns
Write Pulse Width	t_{WP}	45	-	55	-	70	-	ns
Write Recovery Time	t_{WR}	0	-	0	-	0	-	ns
Data to Write Time Overlap	t_{DW}	25	-	30	-	40	-	ns
Data Hold from End of Write Time	t_{DH}	0	-	0	-	0	-	ns
Output Active from End of Write	t_{OW*}	5	-	5	-	5	-	ns
Write to Output in High Z	t_{WHZ*}	-	20	-	25	-	30	ns

*These parameters are guaranteed by device characterization, but not production tested.

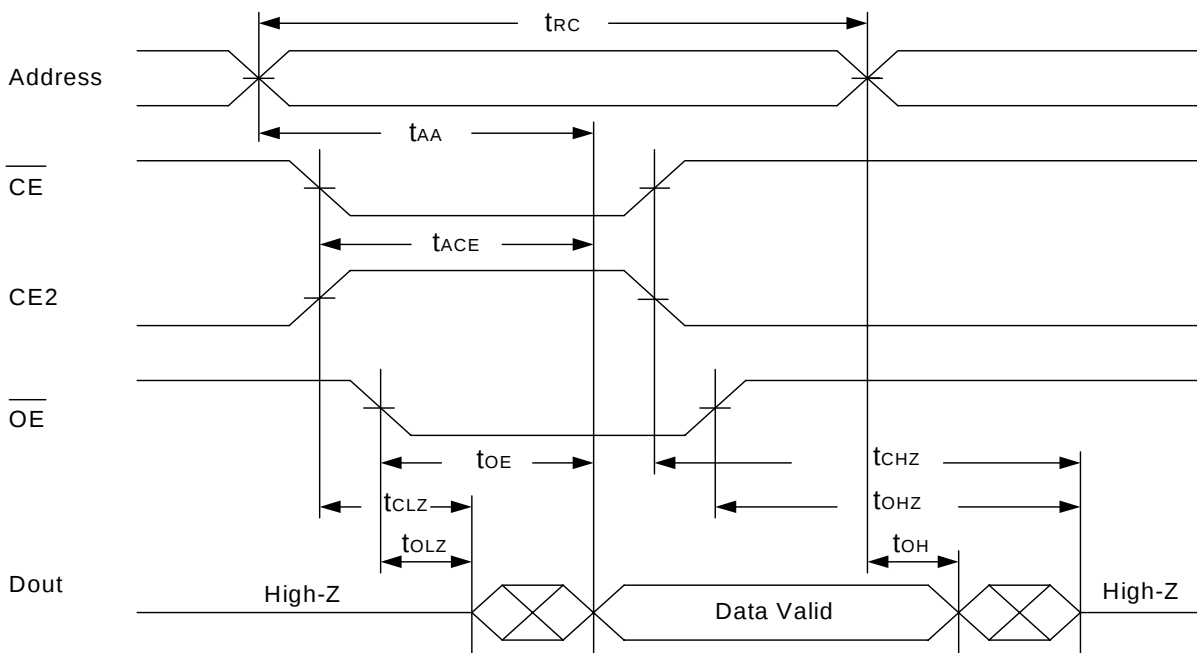


TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2)



READ CYCLE 2 ($\overline{CE}$ and CE2 and $\overline{OE}$ Controlled) (1,3,4,5)



Notes :

1. $\overline{WE}$ is high for read cycle.
2. Device is continuously selected $\overline{OE}$ =low, $\overline{CE}$ =low, CE2=high.
3. Address must be valid prior to or coincident with $\overline{CE}$ =low, CE2=high; otherwise t_{AA} is the limiting parameter.
4. t_{CLZ} , t_{OLZ} , t_{CHZ} and t_{OHZ} are specified with $C_L=5pF$. Transition is measured $\pm 500mV$ from steady state.
5. At any given temperature and voltage condition, t_{CHZ} is less than t_{CLZ} is less than t_{OHZ} is less than t_{OLZ} .

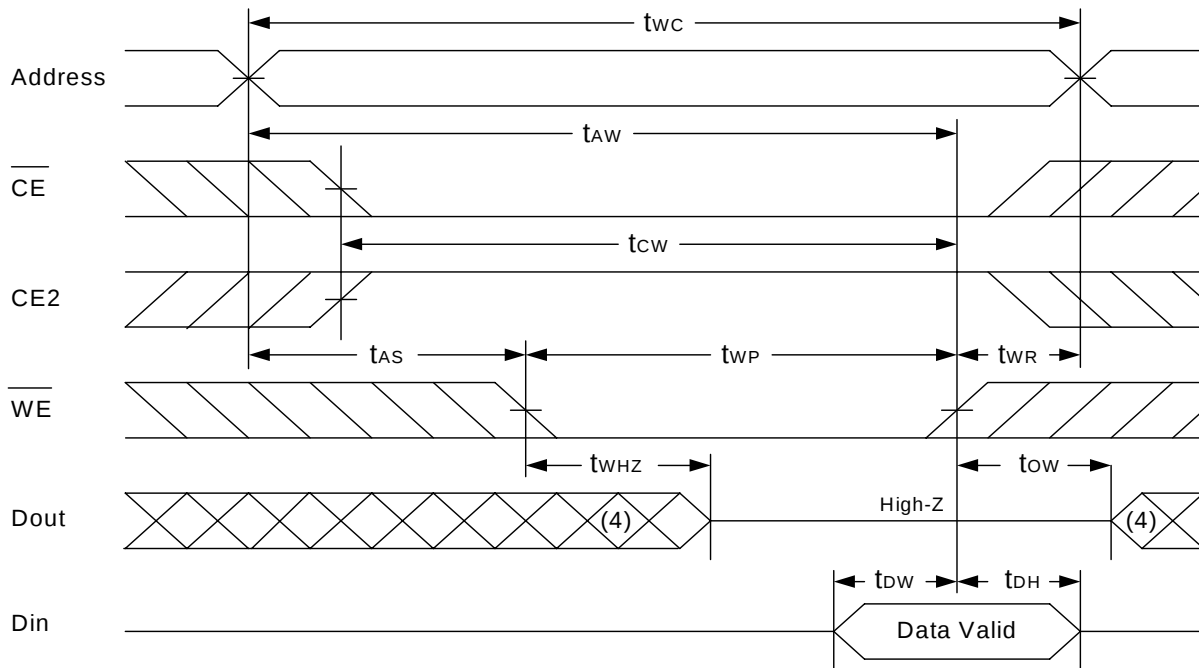


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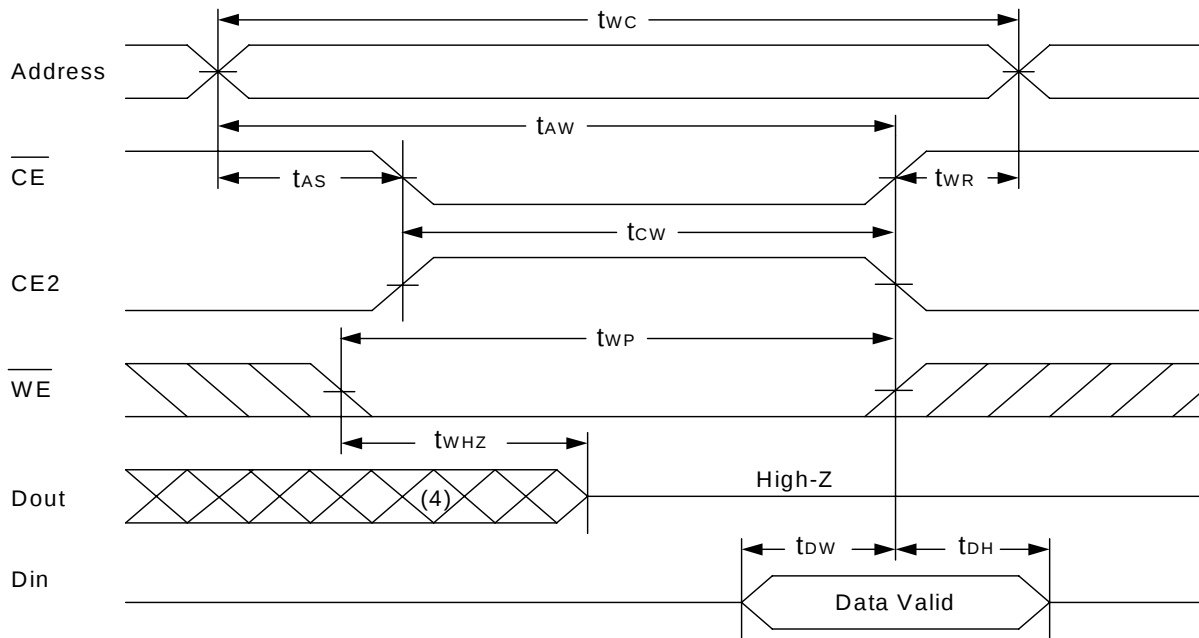
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WRITE CYCLE 1 ($\overline{\text{WE}}$ Controlled) (1,2,3,5,6)



WRITE CYCLE 2 ($\overline{\text{CE}}$ and CE2 Controlled) (1,2,5,6)





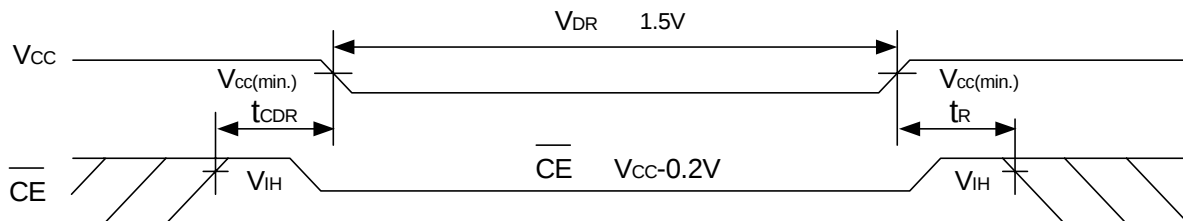
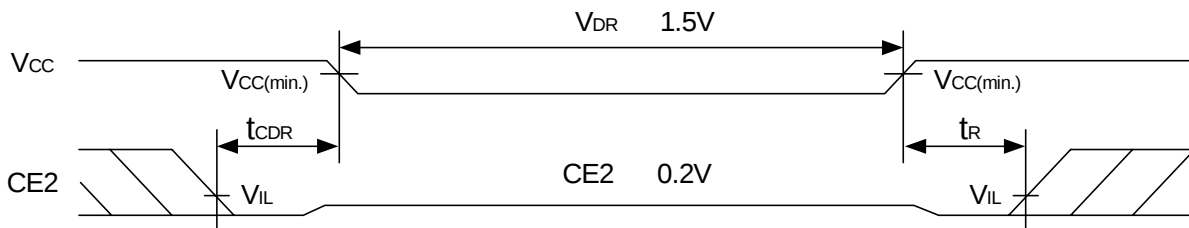
Notes :

1. $\overline{WE}$, $\overline{CE}$ must be high or $\overline{CE2}$ must be low during all address transitions.
2. A write occurs during the overlap of a low $\overline{CE}$, high $\overline{CE2}$, low $\overline{WE}$.
3. During a $\overline{WE}$ controlled write cycle with $\overline{OE}$ low, t_{WP} must be greater than $t_{WHZ} + t_{DW}$ to allow the drivers to turn off and data to be placed on the bus.
4. During this period, I/O pins are in the output state, and input signals must not be applied.
5. If the $\overline{CE}$ low transition and $\overline{CE2}$ high transition occurs simultaneously with or after $\overline{WE}$ low transition, the outputs remain in a high impedance state.
6. t_{OW} and t_{WHZ} are specified with $C_L = 5\text{pF}$. Transition is measured $\pm 500\text{mV}$ from steady state.

DATA RETENTION CHARACTERISTICS ($T_A = 0$ to 70 / -20 to 80 (E))

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Vcc for Data Retention	V_{DR}	$\overline{CE}$ $V_{CC}-0.2\text{V}$ or $\overline{CE2}$ 0.2V	1.5	-	3.6	V
Data Retention Current	I_{DR}	$V_{CC}=1.5\text{V}$ $\overline{CE}$ $V_{CC}-0.2\text{V}$ or $\overline{CE2}$ 0.2V	- L	-	10	μA
			- LL	-	1	μA
Chip Disable to Data Retention Time	t_{CDR}	See Data Retention Waveforms (below)	0	-	-	ns
Recovery Time	t_R		t_{RC}	-	-	ns

DATA RETENTION WAVEFORM

Low Vcc Data Retention Waveform (1) ($\overline{CE}$ controlled)Low Vcc Data Retention Waveform (2) ($\overline{CE2}$ controlled)



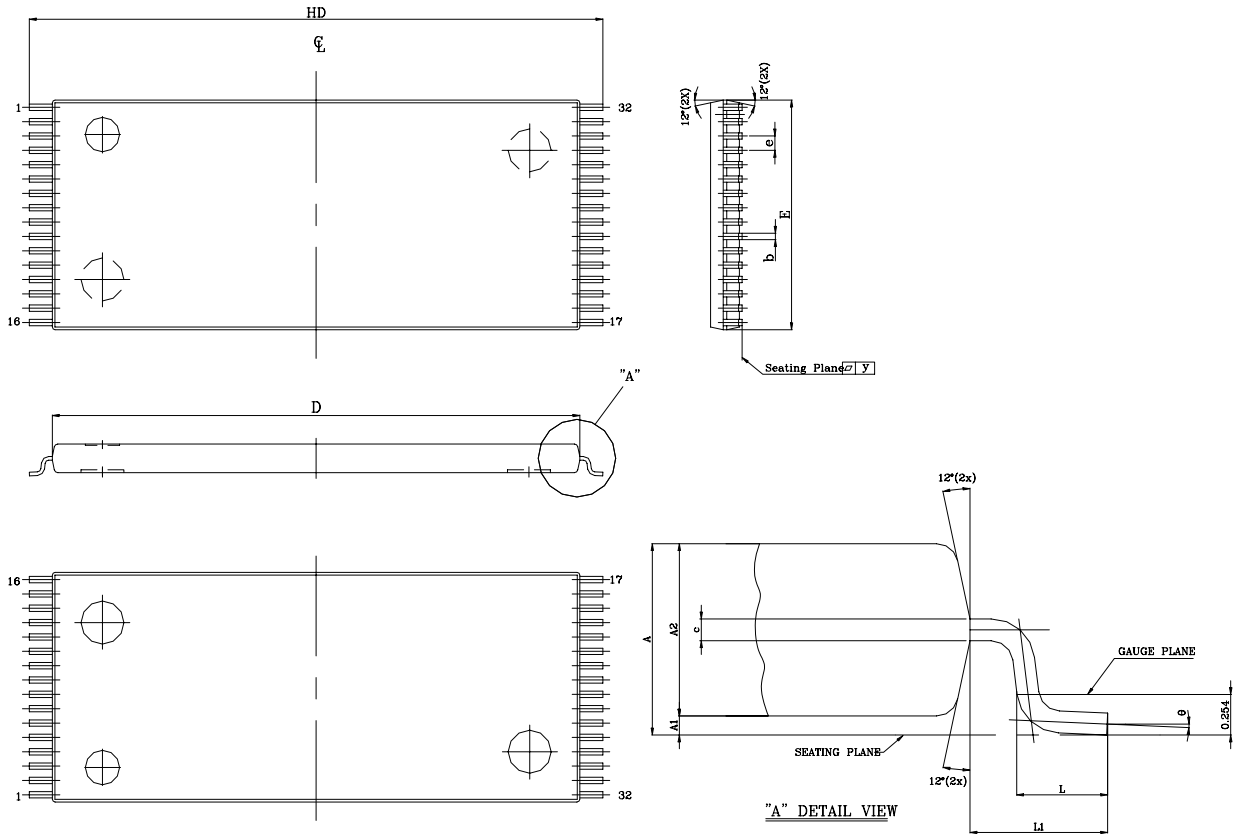
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PACKAGE OUTLINE DIMENSION

32 pin 8mm x 20mm TSOP-I Package Outline Dimension



UNIT SYMBOL	INCH(BASE)	MM(REF)
A	0.047 (MAX)	1.20 (MAX)
A1	0.004 ±0.002	0.10 ±0.05
A2	0.039 ±0.002	1.00 ±0.05
b	0.008 + 0.002 - 0.001	0.20 + 0.05 - 0.03
c	0.005 (TYP)	0.127 (TYP)
D	0.724 ±0.004	18.40 ±0.10
E	0.315 ±0.004	8.00 ±0.10
e	0.020 (TYP)	0.50 (TYP)
HD	0.787 ±0.008	20.00 ±0.20
L	0.0197 ±0.004	0.50 ±0.10
L1	0.0315 ±0.004	0.08 ±0.10
y	0.003 (MAX)	0.076 (MAX)
Θ	0° 5°	0° 5°

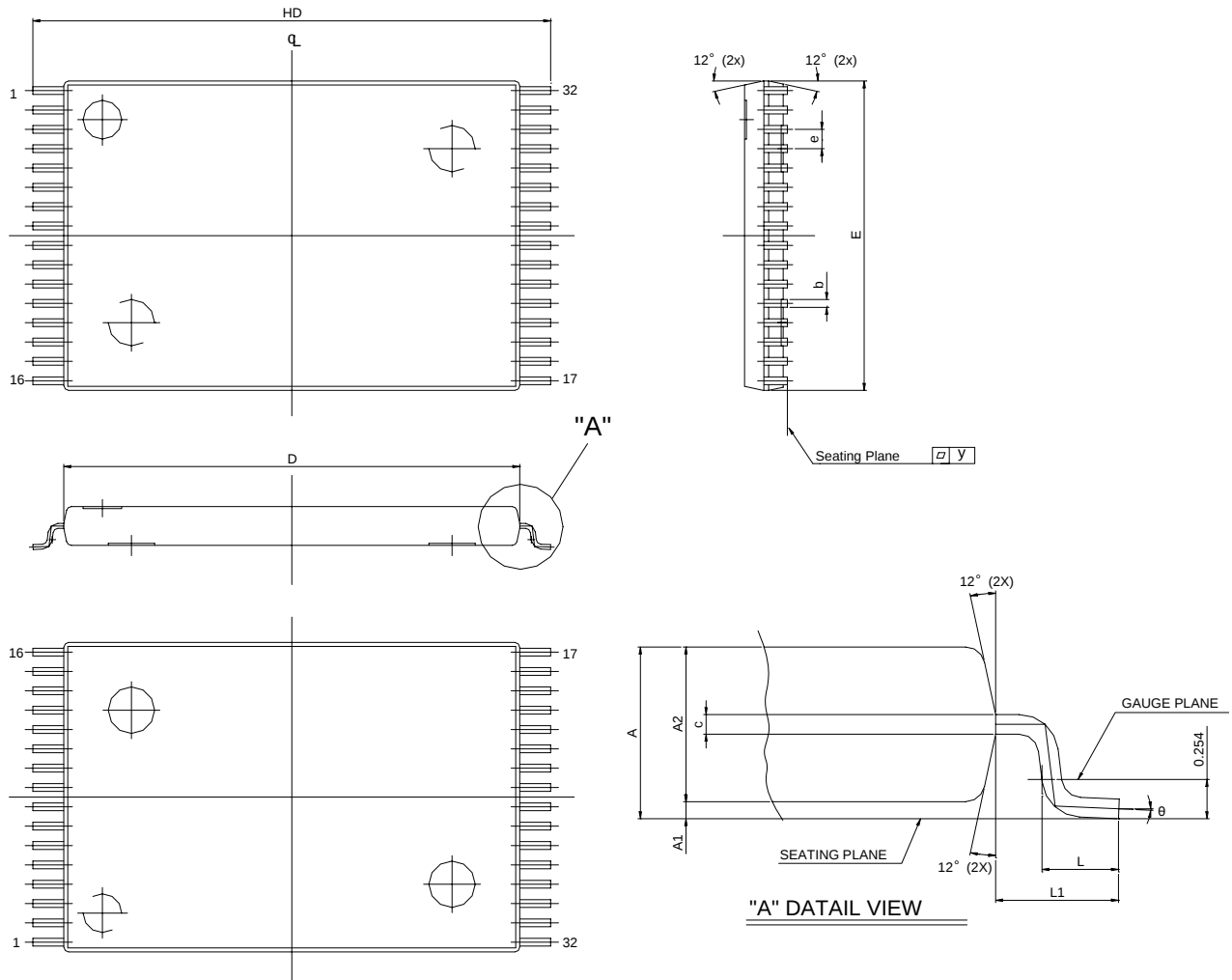


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32 pin 8mm x 13.4mm STSOP Package Outline Dimension



UNIT SYMBOL	INCH(BASE)	MM(REF)
A	0.049 (MAX)	1.25 (MAX)
A1	0.005 ±0.002	0.130 ±0.05
A2	0.039 ±0.002	1.00 ±0.05
b	0.008 ±0.01	0.20±0.025
c	0.005 (TYP)	0.127 (TYP)
D	0.465 ±0.004	11.80 ±0.10
E	0.315 ±0.004	8.00 ±0.10
e	0.020 (TYP)	0.50 (TYP)
HD	0.528±0.008	13.40 ±0.20.
L	0.0197 ±0.004	0.50 ±0.10
L1	0.0315 ±0.004	0.8 ±0.10
y	0.003 (MAX)	0.076 (MAX)
Θ	0° 5°	0° 5°

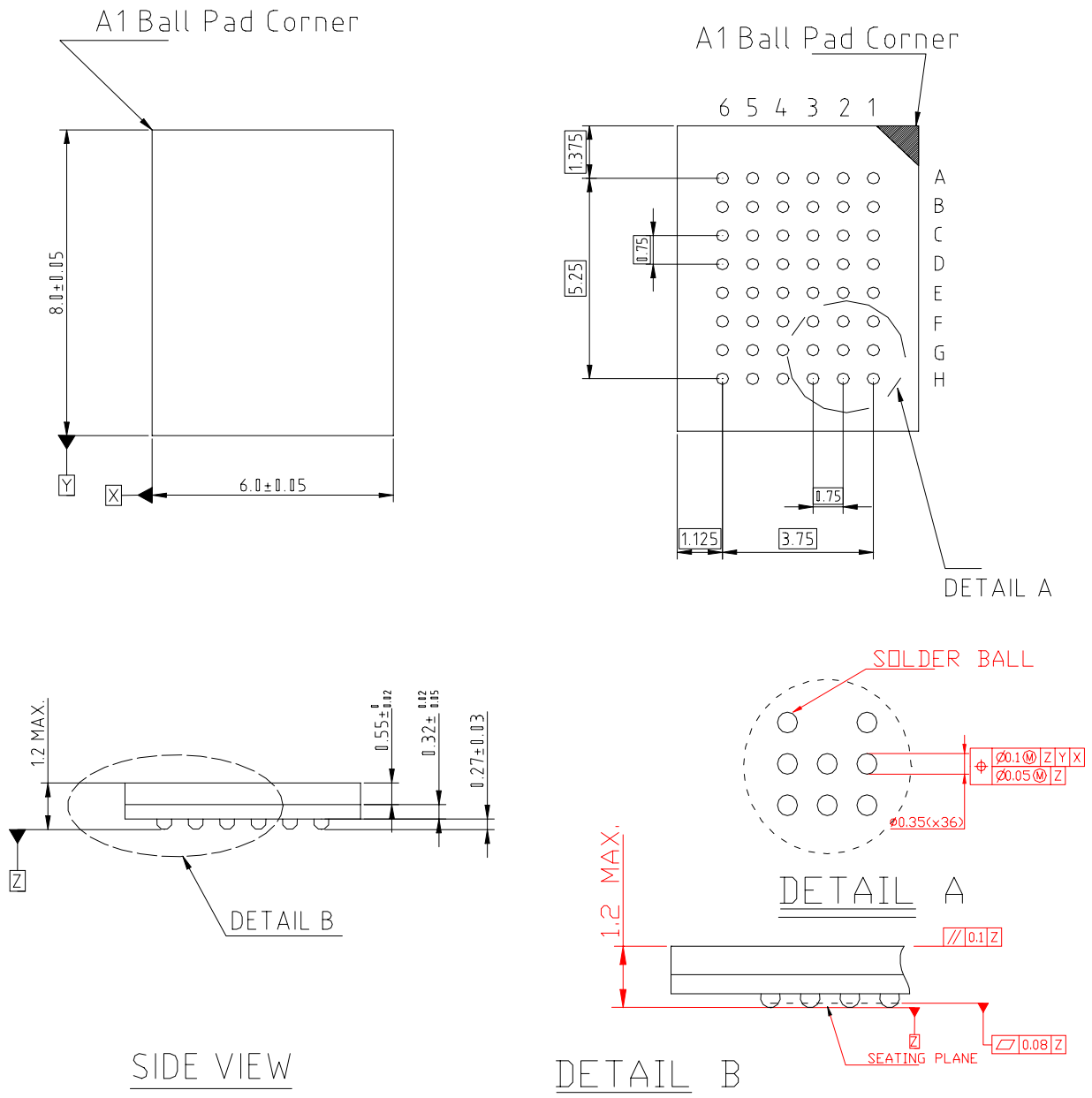


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36 pin 6mm×8mm TFBGA Package Outline Dimension



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UT62L2568**256K X 8 BIT LOW POWER CMOS SRAM****ORDERING INFORMATION****COMMERCIAL TEMPERATURE**

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μ A) TYP.	PACKAGE
UT62L2568LC-55L	55	20	32 PIN TSOP-I
UT62L2568LC-55LL	55	2	32 PIN TSOP-I
UT62L2568LC-70L	70	20	32 PIN TSOP-I
UT62L2568LC-70LL	70	2	32 PIN TSOP-I
UT62L2568LC-100L	100	20	32 PIN TSOP-I
UT62L2568LC-100LL	100	2	32 PIN TSOP-I
UT62L2568LS-55L	55	20	32 PIN STSOP
UT62L2568LS-55LL	55	2	32 PIN STSOP
UT62L2568LS-70L	70	20	32 PIN STSOP
UT62L2568LS-70LL	70	2	32 PIN STSOP
UT62L2568LS-100L	100	20	32 PIN STSOP
UT62L2568LS-100LL	100	2	32 PIN STSOP
UT62L2568BS-55L	55	20	36 PIN TFBGA
UT62L2568BS-55LL	55	2	36 PIN TFBGA
UT62L2568BS-70L	70	20	36 PIN TFBGA
UT62L2568BS-70LL	70	2	36 PIN TFBGA
UT62L2568BS-100L	100	20	36 PIN TFBGA
UT62L2568BS-100LL	100	2	36 PIN TFBGA

EXTENDED TEMPERATURE

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μ A) TYP.	PACKAGE
UT62L2568LC-55LE	55	20	32 PIN TSOP-I
UT62L2568LC-55LLE	55	2	32 PIN TSOP-I
UT62L2568LC-70LE	70	20	32 PIN TSOP-I
UT62L2568LC-70LLE	70	2	32 PIN TSOP-I
UT62L2568LC-100LE	100	20	32 PIN TSOP-I
UT62L2568LC-100LLE	100	2	32 PIN TSOP-I
UT62L2568LS-55LE	55	20	32 PIN STSOP
UT62L2568LS-55LLE	55	2	32 PIN STSOP
UT62L2568LS-70LE	70	20	32 PIN STSOP
UT62L2568LS-70LLE	70	2	32 PIN STSOP
UT62L2568LS-100LE	100	20	32 PIN STSOP
UT62L2568LS-100LLE	100	2	32 PIN STSOP
UT62L2568BS-55LE	55	20	36 PIN TFBGA
UT62L2568BS-55LLE	55	2	36 PIN TFBGA
UT62L2568BS-70LE	70	20	36 PIN TFBGA
UT62L2568BS-70LLE	70	2	36 PIN TFBGA
UT62L2568BS-100LE	100	20	36 PIN TFBGA
UT62L2568BS-100LLE	100	2	36 PIN TFBGA

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PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μ A) TYP.	PACKAGE
UT62L2568LCL-55L	55	20	32 PIN TSOP-I
UT62L2568LCL-55LL	55	2	32 PIN TSOP-I
UT62L2568LCL-70L	70	20	32 PIN TSOP-I
UT62L2568LCL-70LL	70	2	32 PIN TSOP-I
UT62L2568LCL-100L	100	20	32 PIN TSOP-I
UT62L2568LCL-100LL	100	2	32 PIN TSOP-I
UT62L2568LSL-55L	55	20	32 PIN STSOP
UT62L2568LSL-55LL	55	2	32 PIN STSOP
UT62L2568LSL-70L	70	20	32 PIN STSOP
UT62L2568LSL-70LL	70	2	32 PIN STSOP
UT62L2568LSL-100L	100	20	32 PIN STSOP
UT62L2568LSL-100LL	100	2	32 PIN STSOP
UT62L2568BSL-55L	55	20	36 PIN TFBGA
UT62L2568BSL-55LL	55	2	36 PIN TFBGA
UT62L2568BSL-70L	70	20	36 PIN TFBGA
UT62L2568BSL-70LL	70	2	36 PIN TFBGA
UT62L2568BSL-100L	100	20	36 PIN TFBGA
UT62L2568BSL-100LL	100	2	36 PIN TFBGA

EXTENDED TEMPERATURE

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μ A) TYP.	PACKAGE
UT62L2568LCL-55LE	55	20	32 PIN TSOP-I
UT62L2568LCL-55LLE	55	2	32 PIN TSOP-I
UT62L2568LCL-70LE	70	20	32 PIN TSOP-I
UT62L2568LCL-70LLE	70	2	32 PIN TSOP-I
UT62L2568LCL-100LE	100	20	32 PIN TSOP-I
UT62L2568LCL-100LLE	100	2	32 PIN TSOP-I
UT62L2568LSL-55LE	55	20	32 PIN STSOP
UT62L2568LSL-55LLE	55	2	32 PIN STSOP
UT62L2568LSL-70LE	70	20	32 PIN STSOP
UT62L2568LSL-70LLE	70	2	32 PIN STSOP
UT62L2568LSL-100LE	100	20	32 PIN STSOP
UT62L2568LSL-100LLE	100	2	32 PIN STSOP
UT62L2568BSL-55LE	55	20	36 PIN TFBGA
UT62L2568BSL-55LLE	55	2	36 PIN TFBGA
UT62L2568BSL-70LE	70	20	36 PIN TFBGA
UT62L2568BSL-70LLE	70	2	36 PIN TFBGA
UT62L2568BSL-100LE	100	20	36 PIN TFBGA
UT62L2568BSL-100LLE	100	2	36 PIN TFBGA



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